

SURFACE MOUNT SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 1.0 A

Features

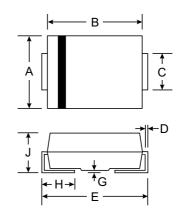
- Diffused junction
- For surface mounted applications
- Low reverse leakage current
- Low forward voltage drop
- High current capability
- Plastic material has UL flammability classification 94V-0

Mechanical Data

- Case: SMA/DO-214AC, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.064 grams (approx.)







SMA(DO-214AC)						
Dim	Min	Max				
Α	2.29	2.92				
В	4.00	4.60				
С	1.27	1.63				
D	0.15	0.31				
E	4.80	5.59				
G	0.10	0.20				
Н	0.76	1.52				
J	2.01	2.62				
All Dimensions in mm						

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

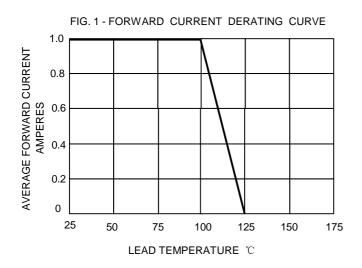
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

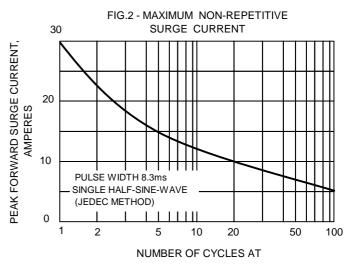
Characteristic	Symbol	M1	M2	МЗ	M4	M5	M6	M7	Unit
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @TL=100 ℃	I(AV)	1.0							А
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed On Rated Load (JEDEC Method)	IFSM	30						А	
Maximum Forward Voltage at 1.0A DC	VF				1.1				V
Maximum DC Reverse Current @TJ=25℃ at Rated DC Blocking Voltage @TJ=100℃	lR				5.0 100				uA
Typical Junction Capacitance (Note1)	Сл				10				pF
Typical Thermal Resistance (Note2)	R JC				30				°C/W
Operating Temperature Range	TJ	-55 to +125						$^{\circ}$	
Storage Temperature Range	Tstg	-55 to +125						$^{\circ}$	

NOTES:1. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

2. Thermal resistance junction to lead.







SINGLE PHASE HALF WAVE 60Hz RESISTIVE OR INDUCTIVE LOAD

